## Adapting Single-Walled Carbon Nanotube-Based Thin-Film Transistors to Flexible Substrates with Electrolyte-Gated Configurations Using a Versatile Tri-Layer Polymer Dielectric

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Supplementary Information

	Before OTS treatment	After OTS treatment
Kapton	$73.1 \pm 1.6^{\circ}$	$98.5 \pm 1.5^{\circ}$
a) $30.619^{+}$ $2.649^{+}$ $2.649^{+}$ $2.649^{+}$ 3.72V $2.649^{+}$ 3.72V 3.72	$\begin{array}{c} C \\ & 60x10^{4} \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & &$	e) 15x10 <sup>2</sup> 
f) 00 V <sub>(0</sub> (V) 50(0 <sup>0</sup> 30(0 <sup>0</sup> -10(0 <sup>0</sup> -15(0 <sup>0</sup> -1	h) 00 V <sub>0</sub> (1) () 00 4500 <sup>4</sup> 5 5 -1500 <sup>4</sup> -1500 <sup>4</sup>	Vm(Y)  I)  00  Vm(Y)    4.5 mtl
V <sub>os</sub> (V) V <sub>os</sub> (V)	V <sub>os</sub> (V)	V <sub>05</sub> (V) V <sub>05</sub> (V)

*Table S1. Comparison of water contact angle (°) before and after treatment with octyltrichlorosilane (OTS)* 

Figure S1. n- (red) and p-type (blue) output characteristics of a tri-layer polymer dielectric TFT fabricated on Kapton® after (a, f) 0 days, (b, g) 3 days, (c, h) 5 days, and (d, i) 7 days exposure to ambient air. (e) n- and (j) p-type output characteristics of a tri-layer polymer dielectric TFT fabricated on quartz after 7 days exposure to ambient air.



Figure S2. Hysteresis obtained from n- and p-type testing over 7 days in ambient air.



*Figure S3. a) Schematic and b) photograph of the PCL-microchannel EG-SWNT-FET device architecture.* 



Figure S4. PCL-microchannel EG-SWNT-FET output characteristics using a) DI water and b) 1X TAE buffer as the electrolyte.



*Figure S5. Non-α-synuclein specific PMMA-microchannel EG-SWNT-FET a) output and b) transfer characteristics using DI water as the electrolyte.* 



Figure S6. Output characteristics of the EG-SWNT-FET sensor using an electrolyte consisting of a) 10 ag/L, b) 1 fg/L, c) 100 fg/L, d) 10 pg/L, e) 1 ng/L, f) 100 ng/L, g) 10 μg/L, and h) 1 mg/L α-synuclein in DI water.



Figure S7. a) Transfer characteristics of the EG-SWNT-FET sensor using an electrolyte consisting of 10 ag/L, 1 fg/L, 100 fg/L, 10 pg/L, 1 ng/L, 100 ng/L, 10 μg/L, and 1 mg/L α-synuclein in DI water. b) Transconductance (g<sub>m</sub>) calculated from the linear regime at all α-synuclein dilutions in DI water.